

Description


The APR348 is a secondary-side MOSFET driver for synchronous rectification, which can effectively reduce the secondary-side rectifier power dissipation and provide a high-performance solution.

The APR348 can support continuous or discontinuous conduction mode (CCM and DCM) and quasi-resonant flyback operation based on a MOSFET operating on-time control technology. This technology provides minimized turn-on and turn-off delay to reduce power loss and keep safe operation without adding any external components or circuitry.

The APR348 can configure into high-side or low-side application to fit various design requirement. It also has specialized light load mode and determines safe driver pulse generation through load detection. The VDD power supply can be charged by VDET or VCC, which means it can be charged by internal PLR (Pulse linear regulator) at low output voltage and charged by internal LDO at high output voltage. Therefore, it can provide a wide output operation voltage from 3.3V to 20V.

The APR348 is available in SOT26 (Type CJ) package.

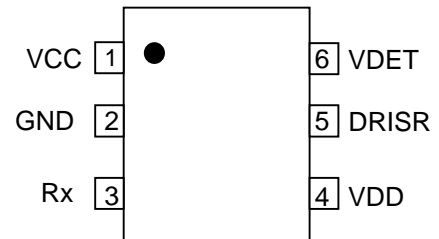
Features

- Synchronous Rectification Controller
- Suited for High-Side and Low-Side Flyback Converters in CCM/DCM/QR Operation
- Minimized Turn-On and Turn-Off Delay
- Internal UVLO Protection
- Light Load Mode Control
- Eliminate False Turn-On with Resonant Ring
- Fewest External Components
- Moisture Sensitivity: MSL Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per M2003 JESD22-B102, Method 208 
- Weight: 0.016/0.017 grams (Approximate)
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Assignments

(Top View)

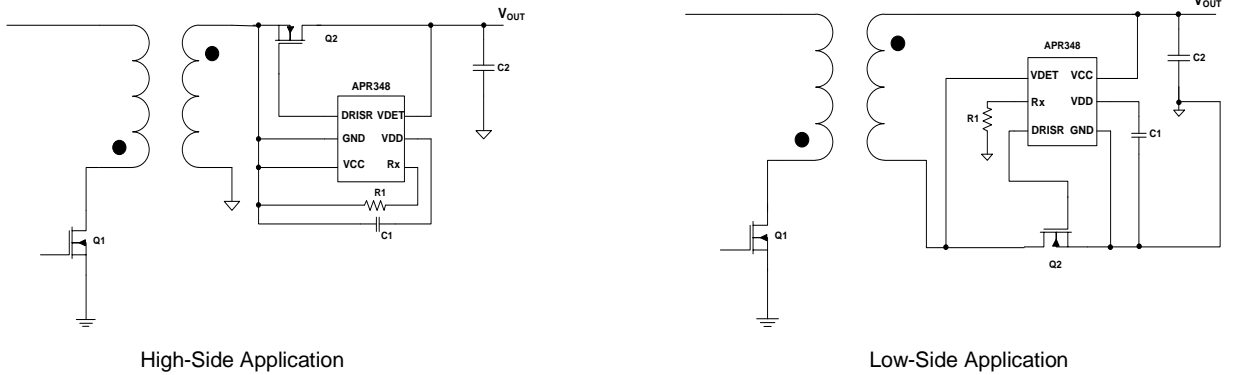


SOT26 (Type CJ)

Applications

- Adapters/Chargers for Cell/Cordless Phones, ADSL Modems, MP3 and Other Portable Apparatus

Typical Applications Circuit



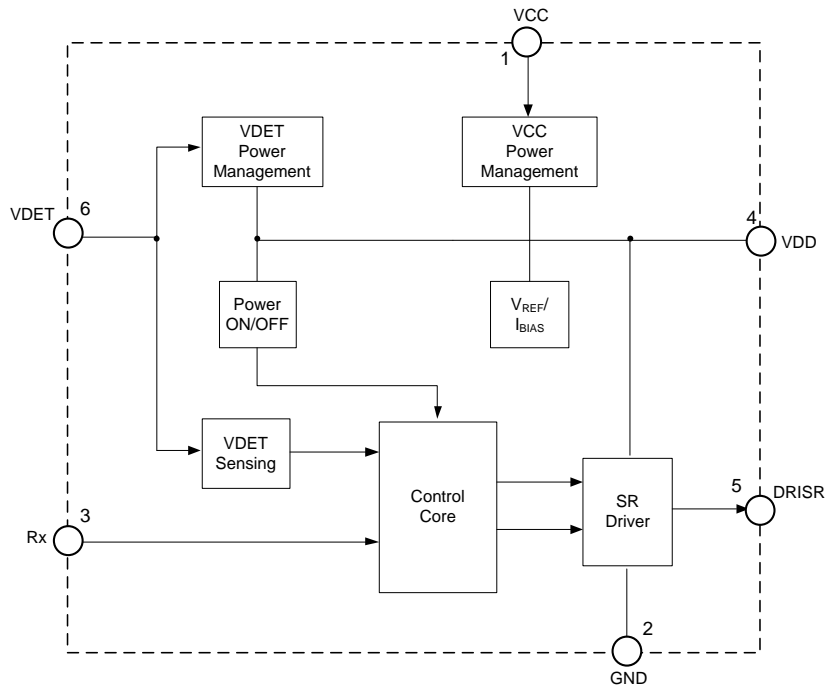
High-Side Application

Low-Side Application

Pin Descriptions

| Pin Number | Pin Name | Function |
|------------|----------|--|
| 1 | VCC | Internal Linear Regulator Input |
| 2 | GND | Ground, also used as FET source sense reference for VDET |
| 3 | Rx | External fixed resistor for Accurate Turn-On Signal |
| 4 | VDD | Linear Regulator Output. It provides bias voltage for the internal logic circuit and the MOSFET driver. Connect this pin to a capacitor. |
| 5 | DRISR | Synchronous Rectification MOSFET Gate Drive |
| 6 | VDET | Synchronous Rectification MOSFET Drain Voltage Sense Input |

Functional Block Diagram



Absolute Maximum Ratings (Note 4)

| Symbol | Parameter | Rating | Unit |
|--------------------|--|-------------|------|
| V _{CC} | Supply Voltage (Note 7) | -0.3 to 28 | V |
| V _{DET} | Voltage at VDET Pin | -0.7 to 150 | V |
| V _{DRISR} | Voltage at DRISR Pin | -0.3 to 7 | V |
| V _{RX} | Voltage at Rx Pin | -0.3 to 7 | V |
| P _D | Power Dissipation at T _A = +25°C | 0.6 | W |
| T _J | Operating Junction Temperature (Note 8) | +150 | °C |
| T _{STG} | Storage Temperature | -65 to +150 | °C |
| T _{LEAD} | Lead Temperature (Soldering, 10s) | +300 | °C |
| θ _{JA} | Thermal Resistance (Junction to Ambient) (Note 5) | 197 | °C/W |
| θ _{JC} | Thermal Resistance (Junction to Case) (Note 5) | 76 | °C/W |
| ESD | Human Body Model (Except VDET Pin) (Note 6) | 6,000 | V |
| | Charge Device Model | 1500 | V |

- Notes:
- Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to *Absolute Maximum Ratings* for extended periods can affect device reliability.
 - Test condition: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch² cooling area.
 - VDET pin are ESD sensitive. (HBM: V_{DET} = 2000V).
 - Setting V_{CC} = 22V in the aging condition. Latch up overvoltage test use V_{CC} = 28V.
 - Setting +85°C in the aging condition.

Electrical Characteristics (@V_{CC} = 5V, T_A = -40°C < T_A < +85°C, unless otherwise specified.)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|--|--|--|-----------------------|------|------|------|
| Supply Voltage (VCC Pin) | | | | | | |
| V _{LDO_DISABLE} | V _{CC} LDO Disable Threshold at V _{CC} Falling | — | 4.25 | 4.55 | 4.85 | V |
| V _{LDO_ENABLE} | V _{CC} LDO Enable Threshold at V _{CC} Rising | — | 4.35 | 4.65 | 4.95 | V |
| V _{LDO_HYS} | LDO Operating Hysteresis at VCC Pin | — | — | 100 | — | mV |
| Supply Linear Regulator (VDD Pin) | | | | | | |
| V _{DD} | Internal Power Supply | V _{CC} = 12V, V _{DET} = 12V | 5 | 5.5 | 6 | V |
| | | V _{CC} = 3V, V _{DET} = 12V | 5.3 | 5.9 | 6.5 | V |
| I _{STARTUP} | V _{DD} Startup Current | V _{CC} = 0, V _{DET} = V _{DD} = V _{DD_ST} - 0.1V | — | 125 | 160 | μA |
| V _{DD_ST} | V _{DD} Startup Voltage | — | 3.55 | 3.75 | 3.95 | V |
| V _{DD_UVLO} | V _{DD} UVLO Voltage | — | 3.30 | 3.50 | 3.70 | V |
| V _{UVLO_HYSTERESIS} | UVLO Hysteresis | — | — | 0.25 | — | V |
| I _{Q_VDD} | Quiescent Current | V _{DD} = 5.5V, V _{CC} = 0 | — | 170 | 220 | μA |
| Synchronous Rectification MOSFET Sense (VDET Pin) | | | | | | |
| V _{THON} | Gate Turn-On Threshold | Voltage at VDET Pin | -130 | -90 | -60 | mV |
| V _{FWD} | Gate Regulation Voltage | Voltage at VDET Pin | -55 | -45 | -35 | mV |
| V _{THOFF} | Gate Turn-Off Threshold | Voltage at VDET Pin | — | -7 | 0 | mV |
| Gate Driver (DRISR Pin) | | | | | | |
| V _{DRISR(High)} | Synchronous Rectification Drive Voltage High | — | V _{DD} - 0.1 | — | — | V |
| V _{DRISR(Low)} | Synchronous Rectification Drive Voltage Low | I _{G_LOAD} = 100mA, V _{DD} = 5V | — | 70 | 140 | mV |
| t _{DON} | Turn-On Delay Time | C _{LOAD} = 2.2nF | — | 30 | 60 | ns |
| t _{DOFF} | Turn-Off Propagation Delay Time | C _{LOAD} = 2.2nF | — | 25 | 45 | ns |
| t _{ON_MIN} | Minimum On-Time | — | 0.8 | 1.2 | 1.6 | μs |
| I _{SOURCE} | Maximum Source Current (Note 9) | — | — | 0.6 | — | A |
| I _{SINK} | Maximum Sink Current (Note 9) | — | — | 3.5 | — | A |
| R _g | Pull-Down Impedent | I _{G_LOAD} = 100mA, V _{DD} = 5V | — | 0.7 | 1.4 | Ω |

Note: 9. These parameters are guaranteed by design and characterization.

Synchronous Rectification Principle Description

Synchronous Rectification MOSFET Turn-On

The APR348 determines the synchronous rectification MOSFET turn-on time by monitoring the MOSFET drain-to-source voltage. Because of the parasitic parameter, the voltage on the MOSFET drain pin has moderate voltage ringing, which may affect the SR controller VDET voltage sense and bring about a turn-on/off fault.

To avoid this conduction fault, the APR348 has internal judge methods to determinate the turn-on moment of synchronous rectification MOSFET. Meanwhile, APR348 has a minimum on-time (t_{ON_MIN} , which is shown in Figure 1) blanking period that keeps the power MOSFET on for a minimum amount of time. When the controlled MOSFET gate turns on, some ringing noises generate. The minimum on-time timer blanks the V_{THOFF} comparator, which keeps the controlled MOSFET on for at least the minimum on-time. During the minimum on-time, the turn-off threshold is blanked unless the V_{DS} ringing voltage goes over 2V during this period.

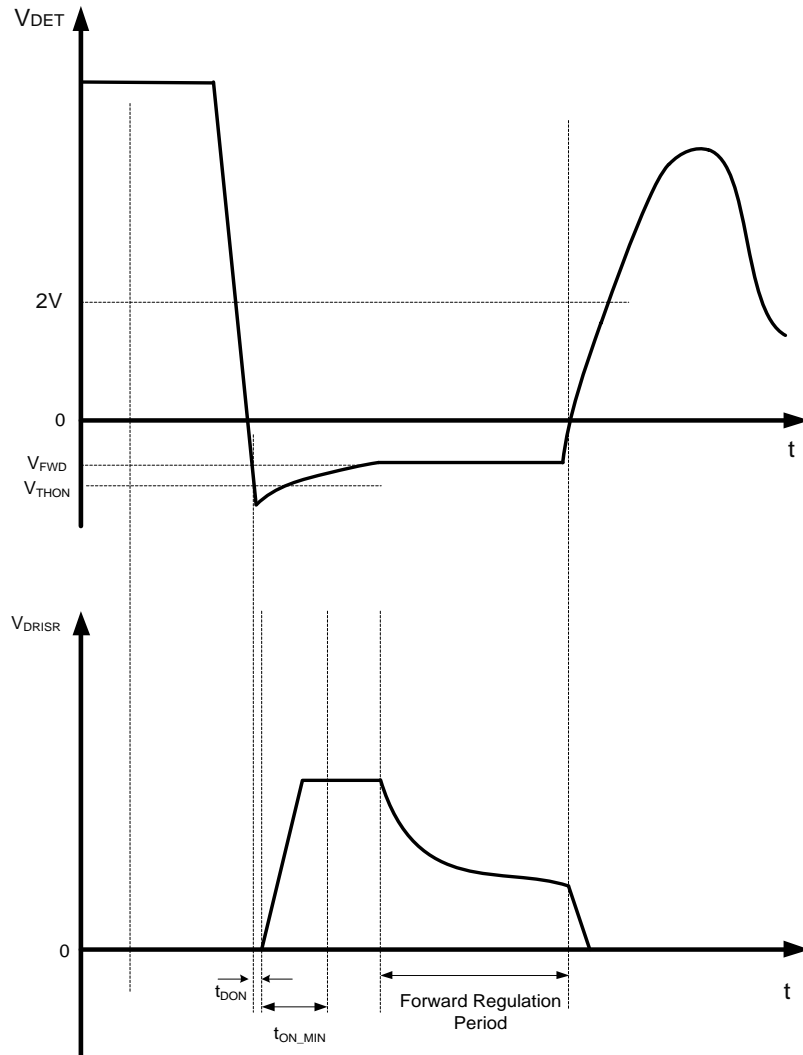


Figure 1. APR348 Switch Period

Synchronous Rectification Principle Description (continued)

The Value and Meaning of Rx Resistance

After the secondary rectifier stops conduction with DCM operation, the primary MOSFET drain-to-source generates a ringing waveform, which results from the resonant of primary inductance and equivalent switch-device output capacitance. This ringing waveform most likely leads to the synchronous rectifier fault conduction. APR348 integrates an accurate turn-on voltage threshold and internal judge criteria to determine whether synchronous rectification MOSFET can turn on or not. Rx is an external resistor, which multiplies with an internal current source to generate an accurate reference for turn-on threshold judgment. Proposed to use 30kΩ to 40kΩ resistance for Rx value.

Synchronous Rectification Forward Regulation and Turn-Off Stage

Once the synchronous rectification gate outputs high levels and the synchronous rectification MOSFET turns on, the secondary-side current goes through synchronous rectification MOSFET. The voltage drop on synchronous rectification MOSFET is found by $R_{DS(ON)} \times$ secondary-side current. After minimum turn-on time t_{ONMIN} , the IC continuously monitors V_{DS} by the VDET pin and generates a pull-down current from the MOSFET gate until $V_{DET} > -45mV$. The MOSFET drain-to-source voltage would remain at around -45mV with the secondary-side current decreasing. Real MOSFET gate voltage depends on the MOSFET characteristics and drain current. When the primary MOSFET turns on, the secondary V_{DS} would rise up. Once V_{DET} rises to trigger the turn-off threshold, the gate signal will be pulled down to GND. The synchronous rectification MOSFET gate voltage drops quickly from a low voltage to zero after a very short turn-off delay.

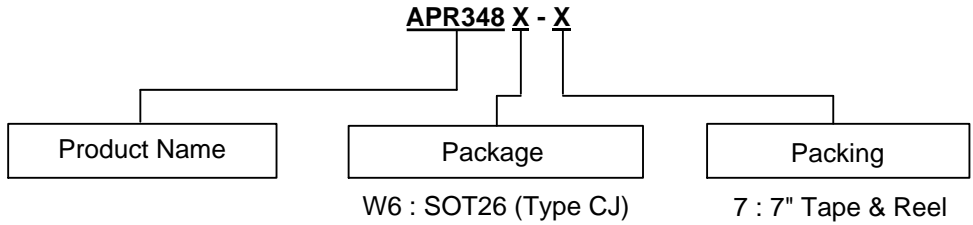
Light Load Mode (LL Mode)

The APR348 provides light-load mode when the system goes into burst or no-load condition with interval-time pulses for low standby loss. The IC internal has two timers, one is 640μs and the other is 2.5ms. When the interval time is between 640μs and 2.5ms, the gate drive outputs will skip the first two cycles. When the interval time is over 2.5ms, gate drive outputs will skip the first eight cycles.

VDD Regulator and UVLO Protection

The VDD is an internal linear regulator output. When the synchronous rectification MOSFET and the IC are connected in low side, the V_{DD} is supplied by both VDET pin and VCC pin. When synchronous rectification MOSFET and IC are connected in high side, the V_{DD} is supplied only via VDET. A large capacitor (typical 4.7μF) at VDD pin is proposed for system design. The APR348 also has the UVLO protection. When V_{DD} drops below V_{DD_UVLO} , the IC will stop working.

Ordering Information

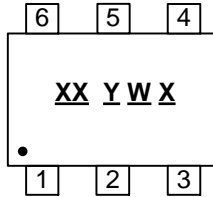


| Package | Temperature Range | Part Number | Identification Code | 7" Tape and Reel | |
|-----------------|-------------------|-------------|---------------------|--------------------|--------------------|
| | | | | Quantity | Part Number Suffix |
| SOT26 (Type CJ) | -40°C to +85°C | APR348W6-7 | DY | 3000/Tape and Reel | -7 |

Marking Information

SOT26 (Type CJ)

(Top View)

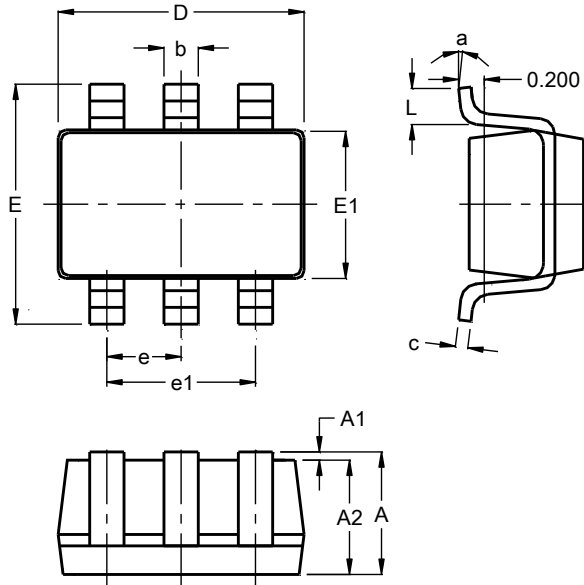


- XX : Identification Code
- Y : Year 0~9
- W : Week : A~Z : 1~26 week;
a~z : 27~52 week; z represents 52 and 53 week
- X : Internal Code

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT26 (Type CJ)

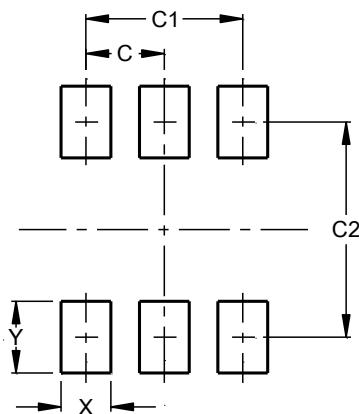


| SOT26 (Type CJ) | | | |
|----------------------|----------|-------|-----|
| Dim | Min | Max | Typ |
| A | 1.050 | 1.250 | -- |
| A1 | 0.00 | 0.10 | -- |
| A2 | 1.050 | 1.150 | -- |
| b | 0.300 | 0.500 | -- |
| c | 0.100 | 0.200 | -- |
| D | 2.820 | 3.020 | -- |
| E | 2.650 | 2.950 | -- |
| E1 | 1.500 | 1.700 | -- |
| e | 0.950BSC | | |
| e1 | 1.800 | 2.000 | -- |
| L | 0.300 | 0.600 | -- |
| a | 0° | 8° | -- |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT26 (Type CJ)



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.95 |
| C1 | 1.90 |
| C2 | 2.40 |
| X | 0.60 |
| Y | 1.00 |

Mechanical Data

- Moisture Sensitivity: Level 1 per JESD22-A113
- Terminals: Finish – Matte Tin Plated Leads, Solderable per JESD22-B102 (Ⓔ)
- Weight: 0.016 grams (Approximate)

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